

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

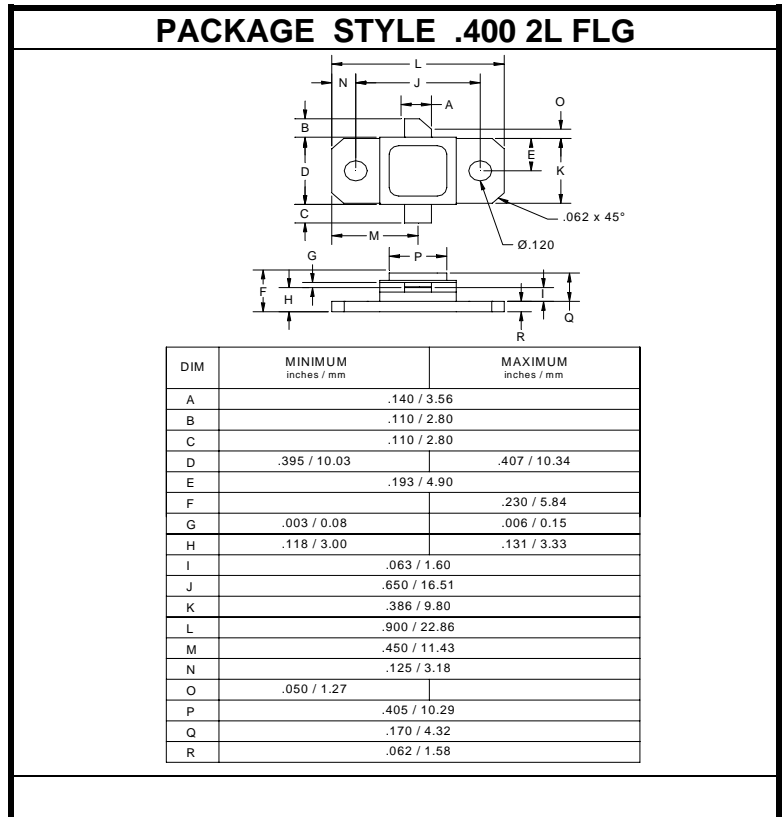
The **ASI MX0912B251Y** is designed for common base Class C broadband TACAN/DME Applications in the 960 to 1215 MHz frequency range.

FEATURES:

- Internal Input/Output Matching Network
- Diffused Emitter Ballasting.
- $P_G = 7$ dB min. at 250 W/ 1215 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	15 A
V_{CB}	65 V
P_{DISS}	690 W @ T_{MB} 75 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.18 °C/W


CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 65$ V			100	mA
I_{CBO}	$V_{CB} = 50$ V			10	mA
I_{CES}	$V_{CE} = 60$ V			100	mA
I_{EBO}	$V_{EB} = 1.5$ V			1.0	mA
P_G	$V_{CC} = 50$ V $P_{OUT} = 235$ W $f = 960 - 1215$ MHz	7.0	7.4		dB
η_C		42	47		%